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(71) **Applicant** *(for all designated States except US)*: **APPLIED MATERIALS, INC.** [US/US]; 3050 Bowers Avenue, Santa Clara, CA 95054 (US).

(72) **Inventors; and**

(75) **Inventors/Applicants** *(for US only)*: **LEE, Sang, M.** [KR/US]; 20681 Forge Way #114, Cupertino, CA 95015 (US). **LEE, Yong-won** [KR/US]; 900 Pepper Tree Lane 414, Santa Clara, CA 95051 (US). **SHEK, Meiyee** [US/US]; 991 N. California Ave., Palo Alto, CA 94303 (US). **XIA, Li-qun** [US/US]; 10221 Western Drive, Cupertino, CA 95014 (US). **WITTY, Derek, R.** [US/US]; 1049 Geronimo Ct., Fremont, CA 94539 (US).

(74) **Agents**: **PATTERSON, B., Todd** et al.; PATTERSON & SHERIDAN, L.L.P., 3040 Post Oak Blvd., Suite 1500, Houston, TX 77056-6582 (US).

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(54) **Title**: ADHESION AND ELECTROMIGRATION IMPROVEMENT BETWEEN DIELECTRIC AND CONDUCTIVE LAYERS

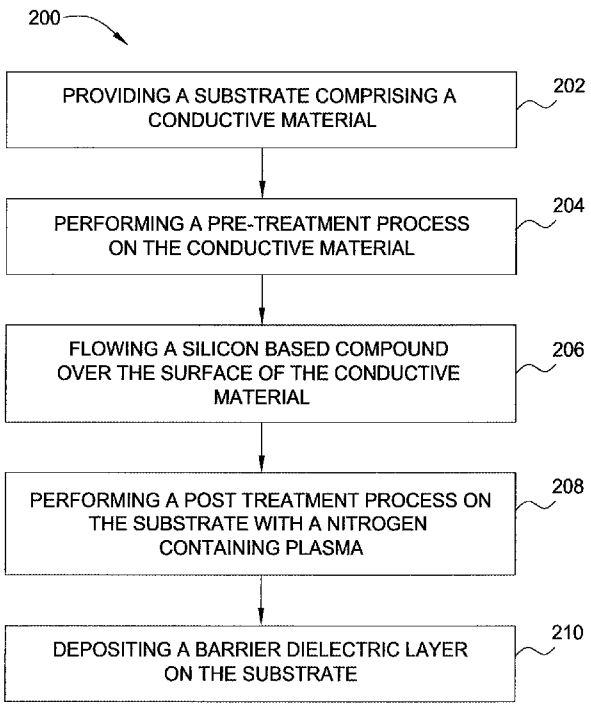

FIG. 2

(57) **Abstract**: A method and apparatus for processing a substrate is provided. The method of processing a substrate includes providing a substrate comprising a conductive material, performing a pre-treatment process on the conductive material, flowing a silicon based compound on the conductive material to form a silicide layer, performing a post treatment process on the silicide layer, and depositing a barrier dielectric layer on the substrate.

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